



PATENT
3313-1017P

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant:	LIU, Chien-Hung et al.	Conf.:	3589
Appl. No.:	10/627,637	Group:	2822
Filed:	July 28, 2003	Examiner:	Mark V. Prenty
For:	METAL OXIDE SEMICONDUCTOR FIELD EFFECT TRANSISTOR (MOSFETS) USED IN INK-JET HEADCHIPS AND METHOD FOR MAKING THE SAME		

LARGE ENTITY TRANSMITTAL FORM

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

September 27, 2004

Sir:

Transmitted herewith is an amendment in the above-identified application.

- ☐ The enclosed document is being transmitted via the Certificate of Mailing provisions of 37 C.F.R. § 1.8.
- ☐ The enclosed document is being transmitted via facsimile.

The fee has been calculated as shown below:

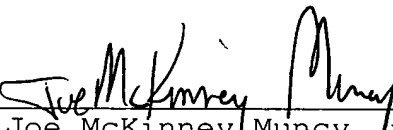
	CLAIMS REMAINING AFTER AMENDMENT		HIGHEST NUMBER PREVIOUSLY PAID FOR		PRESENT EXTRA	RATE	ADDITIONAL FEE
TOTAL	12	-	20	=	0	\$ 18	\$0.00
INDEPENDENT	2	-	3	=	0	\$ 86	\$0.00
<input type="checkbox"/> FIRST PRESENTATION OF A MULTIPLE DEPENDENT CLAIM						\$290	\$0.00
						TOTAL	\$0.00

- ☐ "Petition for () month(s) extension of time pursuant to 37 C.F.R. §§ 1.17 and 1.136(a). \$0.00 for the extension of time.
- ☒ No fee is required.
- ☐ Check(s) in the amount of \$0.00 is(are) enclosed.
- ☐ Please charge Deposit Account No. 02-2448 in the amount of \$0.00. This form is submitted in triplicate.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17; particularly, extension of time fees.

Respectfully submitted,

BIRCH, STEWART, KOLASCH & BIRCH, LLP

By 
Joe McKinney Muncy, #32,334

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KM/asc
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Attachment(s)

(Rev. 02/08/2004)



MS AMENDMENT
PATENT
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Appl. No.: 10/627,637 Group: 2822
Filed: July 28, 2003 Examiner: Mark V. Prenty
For: METAL OXIDE SEMICONDUCTOR FIELD EFFECT
TRANSISTOR (MOSFETS) USED IN INK-JET
HEADCHIPS AND METHOD FOR MAKING THE
SAME

REPLY UNDER 37 C.F.R. § 1.111

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

September 27, 2004

Sir:

Responsive to the July 26, 2004 Office Action, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

This reply includes:

Amendments to the Specification;

Amended Claim Set;

Amendments to the Drawings; and

Remarks.